Development Board Explores Enhancement-Mode GaN FETs

Efficient Power Conversion Corporation introduced the EPC9005 development board to make it easier for users to start designing with a 40 V enhancement-mode gallium nitride (eGaN) field effect transistor (FET) in applications such as high-speed DC-DC power supplies, point-of-load converters, class D audio amplifiers, hard-switched and high frequency circuits.

The EPC9005 development board is a 40 V maximum device voltage, 7 A maximum output current, half bridge with on board gate drives, featuring the EPC2014 40 V eGaN FET. The purpose of this development board is to simplify the evaluation process of the EPC2014 eGaN FET by including all the critical components on a single board that can be easily connected into an existing converter.

The EPC9005 development board is 2” x 1.5” and contains not only two EPC2014 GaN FETs in a half bridge configuration with gate drivers, but also an on board gate drive supply and bypass capacitors. The board contains all critical components and layout for optimal switching performance. There are also various probe points to facilitate simple waveform measurement and efficiency calculation.

A Quick Start Guide, http://epc-co.com/epc/documents/guides/EPC9005_qsg.pdf [1], is included with the EPC9005 development board for reference and ease of use.

EPC9005 development boards are priced at $95.00 each and are available for immediate delivery from Digi-Key at http://digikey.com/Suppliers/us/Efficient-Power-Conversion.page?lang=en [2]

Design Information and Support for eGaN FETs:

• Download 2014 and all EPC eGaN datasheets at http://epc-co.com/epc/Products/eGaNFETs.aspx [3]
• Development boards and other design support available at http://epc-co.com/epc/Products/DemoBoards.aspx [4]
• View eGaN product training support materials at http://epc-co.com/epc/DesignSupport/eGaNFETBasics.aspx [5]
• Application notes for eGaN FETs can be found at http://epc-co.com/epc/Applications/ApplicationBasics.aspx [6]

About EPC
EPC is the leader in enhancement mode Gallium Nitride based power management devices. EPC was the first to introduce enhancement-mode Gallium-Nitride-on-Silicon (eGaN) FETs as power MOSFET replacements in applications such as servers, netbooks, notebooks, LED lighting, cell phones, base stations, flat-panel displays, and class-D audio amplifiers with device performance many times greater than the best silicon power MOSFETs. Visit our web site: www.epc-co.com [7].

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Links:
[1] http://epc-co.com/epc/documents/guides/EPC9005_qsg.pdf
[2] http://digikey.com/Suppliers/us/Efficient-Power-Conversion.page?lang=en
[3] http://epc-co.com/epc/Products/eGaNFETs.aspx
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